STN
ACPAUS, USPATFULL, INSPEC, JAPIO
5/5/03

=> d 16 1 [illegible]

L6 ANSWER [illegible]
AB Silicon [illegible] by chemical vapor deposition (CVD) on seed
particles [illegible] CVD reactor. The reactor has multiple
zones, [illegible] zone where beads are maintained in a submerged
spouted [illegible] upper zone where beads are maintained in a bubbling
fluidized [illegible] portion of the upper zone segregates beads by
size. [illegible] inspecting, sorting and transporting product beads are
also [illegible]

CAS INDEXING IS [illegible] FOR THIS PATENT.
AN [illegible]
TI Silicon [illegible] apparatus
IN Lord, [illegible], WA, United States
Milligan, [illegible], Moses Lake, WA, United States
PA Advanced [illegible] Materials, Inc., Moses Lake, WA, United States (U.S. corporation)
PI US [illegible]
AI US [illegible]
RLI Continuation [illegible] filed on 7 Jun 1995
DT Utility
FS Granted
EXNAM Primary [illegible], Richard
LREP Marquis [illegible] & Shinston, LLP
CLMN Number [illegible]
ECL Exemplary [illegible]
DRWN 14 Drawing [illegible] Drawing Page(s)
LN.CNT 2020
CAS INDEXING IS [illegible] FOR THIS PATENT.

L6 ANSWER [illegible]
AB Silicon [illegible] by chemical vapor deposition (CVD) on seed
particles [illegible] internal to a CVD reactor. The reactor has multiple
zones, [illegible] zone where beads are maintained in a submerged
spouted [illegible] upper zone where beads are maintained in a bubbling
fluidized [illegible] portion of the upper zone segregates beads by
size. [illegible] inspecting, sorting and transporting product beads are
also [illegible]

CAS INDEXING IS [illegible] THIS PATENT.
AN [illegible]
TI [illegible]
IN [illegible]
PA [illegible], WA, [illegible]
PI US [illegible]
AI US [illegible]
DT Utility
FS Granted
EXNAM Primary [illegible] Assistant Examiner: Meeks, Timothy
LREP [illegible]
CLMN [illegible]

L6 [illegible]
AB [illegible]

parti[illegible] with a fluidized bed which is divided into a heating [illegible] zone by a partition. Feed particles in the heating [illegible] by a carrier gas and are heated by microwave[illegible] hand, the reaction zone for the deposition reaction, [illegible] gas, is heated by particle mixing [illegible] zone and the upper section of the heating zone. [illegible] reaction temperature at the reaction zone is maint[illegible] deteriorating the microwave heating of the heating [illegible].

CAS INDEXING I[illegible] PATENT.

AN 95:5[illegible]
TI Fluidi[illegible] by microwaves
IN [illegible]
Song, [illegible], Korea, Republic of
Jeon, [illegible], Korea, Republic of
Kwon, [illegible], Korea, Republic of
Lee, Kan[illegible], Korea, Republic of
Lee, Jae[illegible], Korea, Republic of
Park, [illegible], Korea, Republic of
PA Korea Re[illegible] of Chemical Technology, Daejeon, Korea, Republi[illegible]ration
PI US 53[illegible]
AI US 199[illegible]
RLI Continua[illegible] Ser. No. US 1992-967100, filed on 27 Oct 1992, now aband[illegible]
DT Utility
FS Granted
EXNAM Primary E[illegible], Amalia L.
LREP Jordan a[illegible]
CLMN Number [illegible]
ECL Exempla[illegible]
DRWN 4 Drawin[illegible] Pages
LN.CNT 1447
CAS INDEXING I[illegible] PATENT.

L6 ANSWER [illegible]
AB An impro[illegible] provided for the deposition of high-purity silicon on sil[illegible] silicon source gases in a fluidized bed reactor [illegible] into a heating zone and a reaction zone by a partit[illegible] in the heating zone are fluidized by a carrier [illegible] and are heated by microwaves. On the other hand, [illegible] the deposition of silicon, through which [illegible] is heated by particle mixing [illegible] and the upper section of the heating zone. [illegible] reaction temperature at the reaction zone [illegible] the microwave heating of the heating [illegible].

CAS INDEXING I[illegible] PATENT.
AN [illegible]
TI Heating [illegible] by microwaves
IN Kim, [illegible], Republic of
[illegible], Republic of
[illegible], Republic of

AI [illegible]
RLI Conti[illegible] [illegible], filed on 27 Oct 1992, now [illegible]
DT [illegible]
FS [illegible]
EXNAM Primar[illegible], Ar[illegible]
LREP [illegible]
CLMN Number [illegible]
ECL Exemp[illegible]
DRWN 4 Drawin[illegible] 4 Drawing Pages
LN.CNT [illegible]
CAS INDEXING [illegible] THIS PATENT.

L6 ANSWER [illegible]
AB Embodim[illegible] [illegible]dynamic processors are disclosed which utilize [illegible] cathode-buffer, anodeionizer and vacuum [illegible] structures to transform a working fluid into a beam [illegible] plasma. The beam is controlled both in its size and di[illegible] magnets which are mounted in surrounding relati[illegible], vacuum insulator/isolators and plasma beam p[illegible], the processor may be utilized in many diverse appli[illegible] separation of ions of differing weights and/or [illegible] and the deposition of any ionizable pure materi[illegible] applications of the processor are disclosed.

AN [illegible]
TI Magnet[illegible] [illegible], applications thereof and methods
IN Cann, [illegible] Beach, CA, United States
PA Celest[illegible], United States (U.S. corporation)
PI US 34[illegible]
US 466[illegible] [illegible]8 (Original)
AI US 19[illegible]
US 19[illegible] (Original)
RLI Continu[illegible] Ser. No. US 19[illegible], filed on 28 Jul 1989, now abando[illegible] continuation-in part of Ser. No. US 1989-[illegible], filed [illegible] abandoned
DT Reissu[illegible]
FS Grante[illegible]
EXNAM Primary [illegible], T[illegible]
LREP Wel[illegible]
CLMN Number [illegible]
ECL Exempl[illegible]
DRWN [illegible]
LN.CNT [illegible]

L6 AN[illegible]
AB A [illegible] flow in temperature in the apparat[illegible], and an apparatus outer wall temperature are [illegible], the interior of the apparatus being under [illegible] and heated by a heater, an analysis [illegible] the apparatus and other values, and a [illegible], and a simulation is carried out [illegible] heater [illegible]

A[illegible]

STN SEARCH 5/5/03

AN

TI System ... thermal analysis of a fluid
inside ...

IN Ishida, ... Japan
Yama..., ... Japan
...
Katan..., ... Japan
Okada, ... Japan
Yajima, ... Japan

PA Mitsu... Company, both of, Japan (non-U.S. corporation)
Mitsu..., both of, Japan (non-U.S. corporation)

PI US ...

AI US ...

PRAI JP ...
JP ...

DT Utility

FS Granted

EXNAM Primary ..., Robert

LREP Burgess, ...

CLMN Number ...

ECL Exemplary ...

DRWN ... Drawing Page(s)

LN.CNT 733

CAS INDEXING ... PATENT.

L6 ANSWER ...

AB In a process ... enzyme crystals, small crystals are continuously ... from a crystallizer, dissolved and returned to the crystallizer ... in a supersaturated state. The method permits the growing ... crystalline enzymes of uniform size of about 0.5 to 1 mm. ... seeded with crystalline enzymes by placing a solid ... crystallizer such that crystals deposit on the solid ... preferably used to produce crystalline glucose ...

AN

TI Method ... glucose isomerase

IN Visuri, ... Finland

PA Stabra ... (non-U.S. corporation)

PI US ...

AI US ...

DT Utility

FS Granted

EXNAM Primary ...

LREP ...

CLMN Number ...

ECL Exemp...

DRWN ...

LN.CNT 744

L6 ANSWER ...

AB The process ... to an improved process for producing ...

BEST AVAILABLE COPY

CAS INDEXING ... THIS PATENT.
AN [illegible]
TI [illegible] high purity polycrystalline silicon
IN [illegible], NY, United States
[illegible], WA, United States
[illegible]
[illegible], WA, United States
PA [illegible], Danbury, CT, United States U.S. corporation
PI US [illegible]
AI US [illegible]
DT Utility
FS Granted
EXNAM Primary Ex[illegible], William R.; Assistant Examiner: Griffis, Andrew
LREP Reinisch, [illegible]
CLMN Number [illegible]
ECL Exemplary [illegible]
DRWN 20 Drawing [illegible] Drawing Pages
LN.CNT 895
CAS INDEXING ... THIS PATENT.

L6 ANSWER [illegible]
AB Embodiments [illegible] magnetohydrodynamic processors are disclosed which utilize [illegible] cathode buffer, anodeionizer and vacuum [illegible] structures to transform a working fluid into a beam [illegible]. The beam is controlled both in its size and direction [illegible] magnets which are mounted in surrounding relation [illegible], vacuum insulator/isolators and plasma beam [illegible], the processor may be utilized in many diverse applications [illegible] the separation of ions of differing weights and/or [illegible] potentials and the deposition of any ionizable pure material [illegible] applications of the processor are disclosed.

AN [illegible]
TI Magneto[illegible], applications thereof and methods
IN Cann, [illegible] East, Irvine, CA, United States 92714
PI US 46[illegible]
AI US [illegible]
RLI Continuation [illegible] Ser. No. US 1980-21 241, filed on 25 Nov 1980, now aban[illegible]
DT Utility
FS Granted
EXNAM Primary [illegible]
LREP [illegible]
CLMN [illegible]
ECL [illegible]
DRWN [illegible]
LN.CNT [illegible]

L6 ANSWER [illegible]
AB The [illegible] of silicon bodies from a melt and [illegible] interface with a mixture of an [illegible]

BEST AVAILABLE COPY

PI [illegible]
AI [illegible]
RLI [illegible] 78, filed on [illegible] Mar [illegible],
[illegible]
DT [illegible]
FS [illegible]
EXNAM [illegible] am H.
LREP [illegible]
CLMN [illegible]
ECL [illegible]
DRWN [illegible] Page[illegible]
LN.CNT [illegible]
CAS INDEXING [illegible] PATENT

L6 ANSWER [illegible]
AB In the [illegible] at an elevated temperature, a stream [illegible] mixture of an oxygen-containing first gas and a [illegible] the processing chamber. The first gas is one which [illegible] under the conditions in the chamber to form [illegible] gas. The second gas is one which is not harmful [illegible] conditions in the chamber. Substantially equili[illegible] established in the chamber so that the disso[illegible] oxygen occurs reversibly. The partial press[illegible] is sensed in the chamber during proce[illegible]. In response to the P.sub.O.sbsb.2 level, the ratio [illegible] the oxygen containing gas and the second gas [illegible] in the P.sub.O.sbsb.2 at a level less than [illegible], and usually no greater than about [illegible] the density of oxygen-related defects in the p[illegible] acceptably low. Oxygen related defects in the [illegible] reduced. If graphite structures are present in the [illegible] chamber, they are preferably coated with [illegible] will stand the high temperature and will [illegible] coming into contact with the hot graph[illegible] are thereby also [illegible]

CAS INDEXING [illegible] PATENT.
AN [illegible]
TI Cont[illegible] related crystal defects in silicon pro[illegible]
IN [illegible]
PA [illegible]
PI [illegible]
AI [illegible]
DT [illegible]
FS [illegible]
EXNAM [illegible] am H.
LREP [illegible]
CLMN [illegible]
ECL [illegible]
DRWN [illegible]

BEST AVAILABLE COPY

[illegible] MAY

```
L1      [illegible]        [illegible]  [illegible]
L2      [illegible]        [illegible]  [illegible]
L3      [illegible]        [illegible]  [illegible]
L4      [illegible]        [illegible]  [illegible]
L5      [illegible]        [illegible] DETERMIN[illegible] OR [illegible] FLO
L6      [illegible]        [illegible] AND [illegible]

=>
```

BEST AVAILABLE COPY

This Page is Inserted by IFW Indexing and Scanning Operations and is not part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- ☐ BLACK BORDERS
- ☐ IMAGE CUT OFF AT TOP, BOTTOM OR SIDES
- ■ FADED TEXT OR DRAWING
- ☐ BLURRED OR ILLEGIBLE TEXT OR DRAWING
- ☐ SKEWED/SLANTED IMAGES
- ☐ COLOR OR BLACK AND WHITE PHOTOGRAPHS
- ☐ GRAY SCALE DOCUMENTS
- ☐ LINES OR MARKS ON ORIGINAL DOCUMENT
- ☐ REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY
- ☐ OTHER: ______________________

IMAGES ARE BEST AVAILABLE COPY.
As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.